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Kind regards,

Team Nexperia



# **BAS21W** series

# High-voltage switching diodes Rev. 01 — 9 October 2009

**Product data sheet** 

## **Product profile**

### 1.1 General description

High-voltage switching diodes, encapsulated in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Configuration	Package		Package	
		NXP	JEDEC	configuration	
BAS21W	single	SOT323	SC-70	very small	
BAS21AW	dual common anode				
BAS21SW	dual series				

#### 1.2 Features

- High switching speed:  $t_{rr} \le 50$  ns
- Low leakage current
- High reverse voltage: V<sub>R</sub> ≤ 250 V
- Low capacitance: C<sub>d</sub> ≤ 2 pF
- Very small SMD plastic package
- AEC-Q101 qualified

#### 1.3 Applications

- High-speed switching
- General-purpose switching
- Voltage clamping
- Reverse polarity protection

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode				,,		
I <sub>F</sub>	forward current		<u>[1]</u> -	-	225	mA
I <sub>R</sub>	reverse current	$V_{R} = 200 \text{ V}$	-	-	100	nA
$V_R$	reverse voltage		-	-	250	V
t <sub>rr</sub>	reverse recovery time		[2] _	-	50	ns

<sup>[1]</sup> Single diode loaded.



<sup>[2]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

## 2. Pinning information

Table 3. **Pinning** Pin **Description** Simplified outline **Graphic symbol** BAS21W anode not connected 3 cathode BAS21AW cathode (diode 1) 2 cathode (diode 2) 3 common anode 006aab099 BAS21SW anode (diode 1) 2 cathode (diode 2) cathode (diode 1), anode (diode 2) 本

# 3. Ordering information

Table 4. Ordering information

Type number	r Package					
	Name	Description	Version			
BAS21W	SC-70	plastic surface-mounted package; 3 leads	SOT323			
BAS21AW						
BAS21SW						

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006aaa763

#### **Marking** 4.

Table 5. **Marking codes** 

Type number	Marking code <sup>[1]</sup>
BAS21W	X4*
BAS21AW	X6*
BAS21SW	X5*

<sup>[1] \* = -:</sup> made in Hong Kong

#### **Limiting values** 5.

Table 6. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_{R}$	reverse voltage		-	250	V
I <sub>F</sub>	forward current		<u>[1]</u> _	225	mA
			[2] _	125	mA
I <sub>FRM</sub>	repetitive peak forward current		-	625	mA
I <sub>FSM</sub> non-repetitive peak forwa		square wave	[3]		
	current	$t_p = 1 \mu s$	-	9	Α
		$t_p = 100 \mu s$	-	3	Α
		$t_p = 10 \text{ ms}$	-	1.7	Α
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[4]</u> _	200	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

<sup>[1]</sup> Single diode loaded.

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

<sup>[2]</sup> Double diode loaded.

<sup>[3]</sup>  $T_i = 25$  °C prior to surge.

<sup>[4]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	625	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	300	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

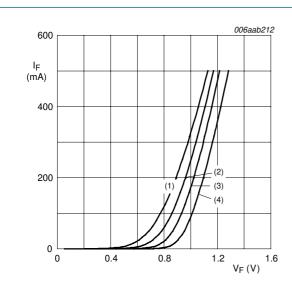
## 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

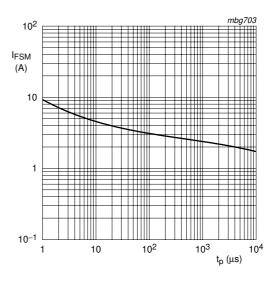
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	•					
$V_{F}$	forward voltage	I <sub>F</sub> = 100 mA	-	-	1.0	V
		$I_F = 200 \text{ mA}$	-	-	1.25	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V	-	-	100	nA
		$V_R = 200 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	2	pF
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> _	-	50	ns

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

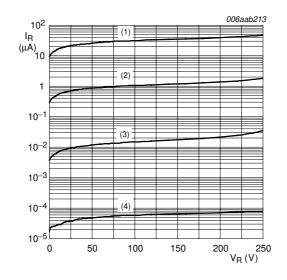
Fig 1. Forward current as a function of forward voltage; typical values



Based on square wave currents.

 $T_i = 25 \,^{\circ}C$ ; prior to surge

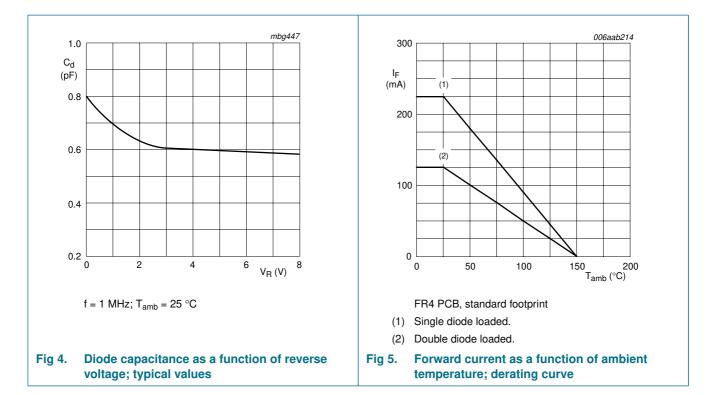
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



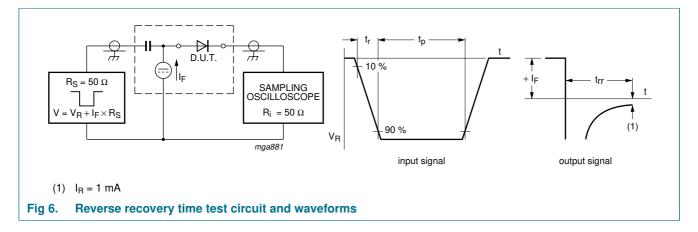
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 3. Reverse current as a function of reverse voltage; typical values

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## 8. Test information

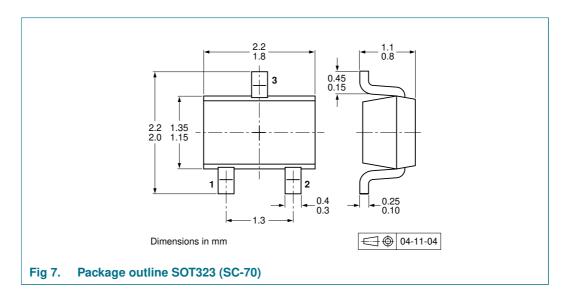


#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 9. Package outline



# 10. Packing information

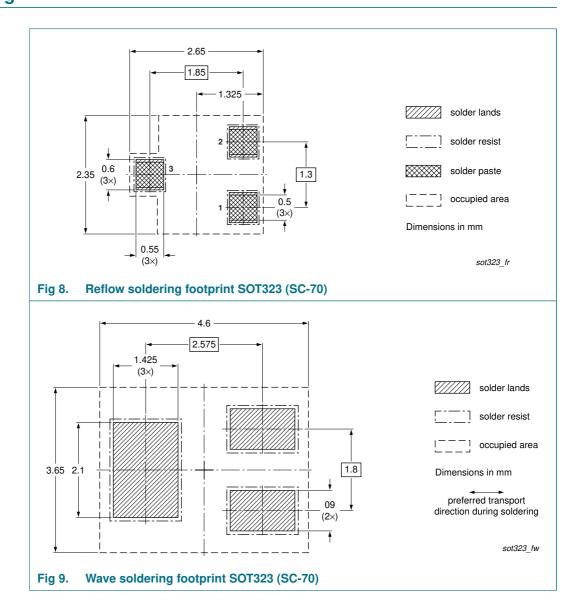
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
BAS21W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135
BAS21AW				
BAS21SW				

[1] For further information and the availability of packing methods, see Section 14.

## 11. Soldering



**BAS21W** series

High-voltage switching diodes

# 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS21W_SER_1	20091009	Product data sheet	-	-

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#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **BAS21W** series

## High-voltage switching diodes

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